

MOSFET

OptiMOS™ 3 Linear FET, 200 V

Features

- Ideal for hot-swap and e-fuse applications
- Very low on-resistance $R_{DS(on)}$
- Wide safe operating area SOA
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21

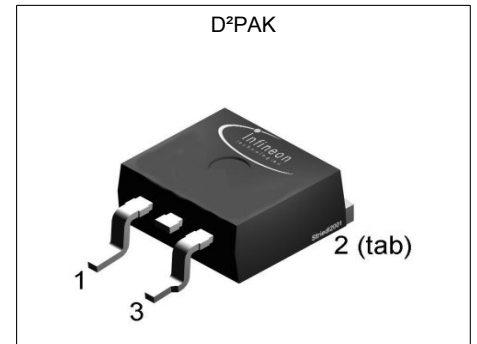
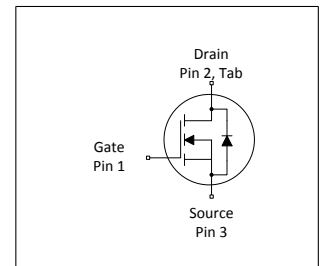


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	200	V
$R_{DS(on),max}$	11	mΩ
I_D	88	A
I_{pulse} ($V_{DS}=56$ V, $t_p=10$ ms)	8.7	A



Type / Ordering Code	Package	Marking	Related Links
IPB110N20N3LF	PG-TO 263-3	110N20LF	-

¹⁾ J-STD20 and JESD22

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	88 61 11	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$, $R_{thJA}=40\text{ K/W}^{1)}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	352	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ³⁾	E_{AS}	-	-	560	mJ	$I_D=80\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	250	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.3	0.5	K/W	-
Device on PCB, minimal footprint	R_{thJA}	-	-	62	K/W	-
Device on PCB, 6 cm ² cooling area ¹⁾	R_{thJA}	-	-	40	K/W	-

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See Diagram 3 for more detailed information

³⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	200	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3.2	4.2	V	$V_{DS}=V_{GS}$, $I_D=260\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	1 10	2 100	μA	$V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	2 -2	5 -5	μA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ $V_{GS}=-10\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	9.8	11	$\text{m}\Omega$	$V_{GS}=10\text{ V}$, $I_D=88\text{ A}$
Gate resistance ¹⁾	R_G	-	60	90	Ω	-
Transconductance	g_{fs}	16	31	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=44\text{ A}$

Table 5 Dynamic characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	500	650	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	390	510	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	5	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	6	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=44\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	70	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=44\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	79	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=44\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	26	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=44\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	4	-	nC	$V_{DD}=100\text{ V}$, $I_D=22\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	51	-	nC	$V_{DD}=100\text{ V}$, $I_D=22\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	76	-	nC	$V_{DD}=100\text{ V}$, $I_D=22\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	6.8	-	V	$V_{DD}=100\text{ V}$, $I_D=22\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	154	-	nC	$V_{DD}=100\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	88	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	352	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.95	1.2	V	$V_{GS}=0\text{ V}, I_F=88\text{ A}, T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	145	-	ns	$V_R=100\text{ V}, I_F=44\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	770	-	nC	$V_R=100\text{ V}, I_F=44\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

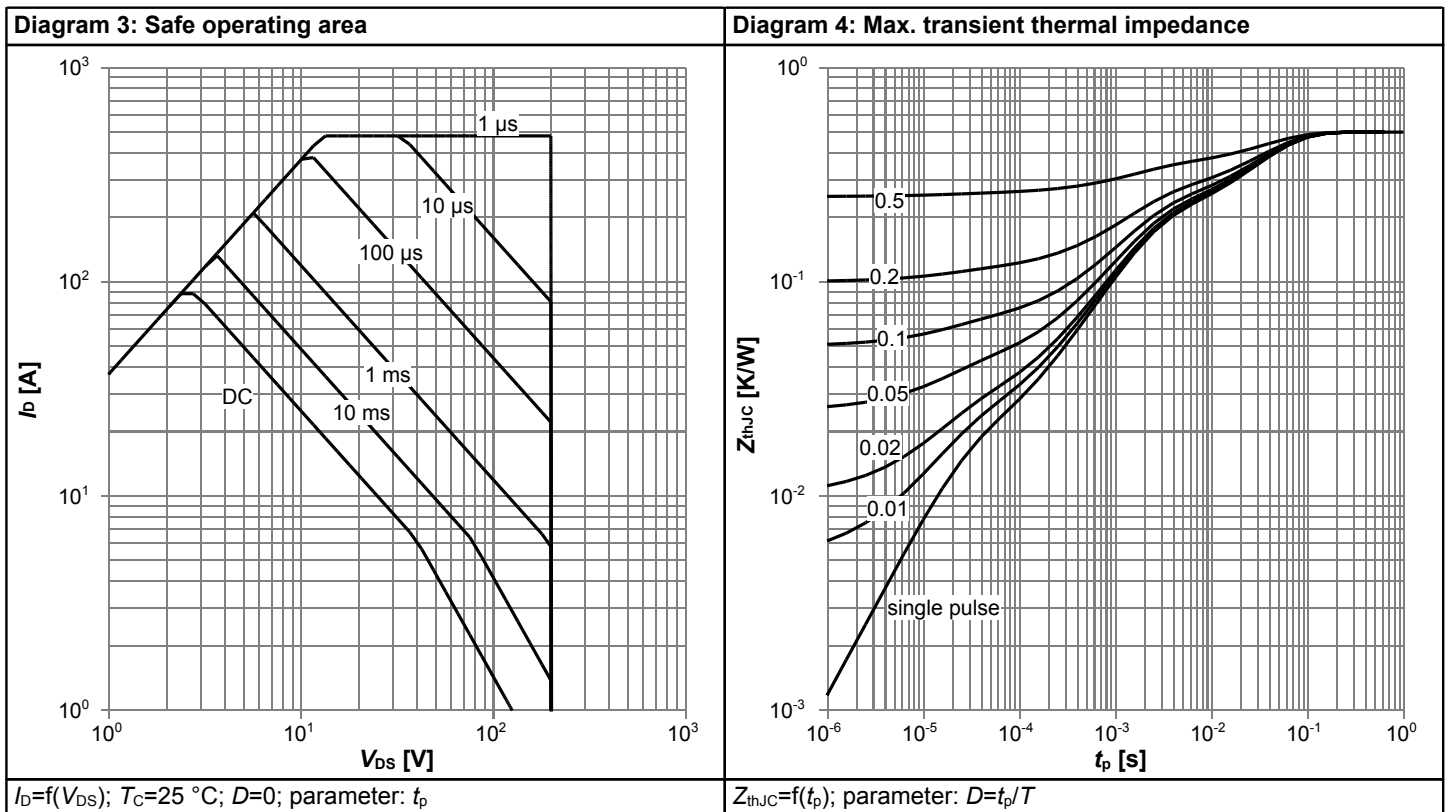
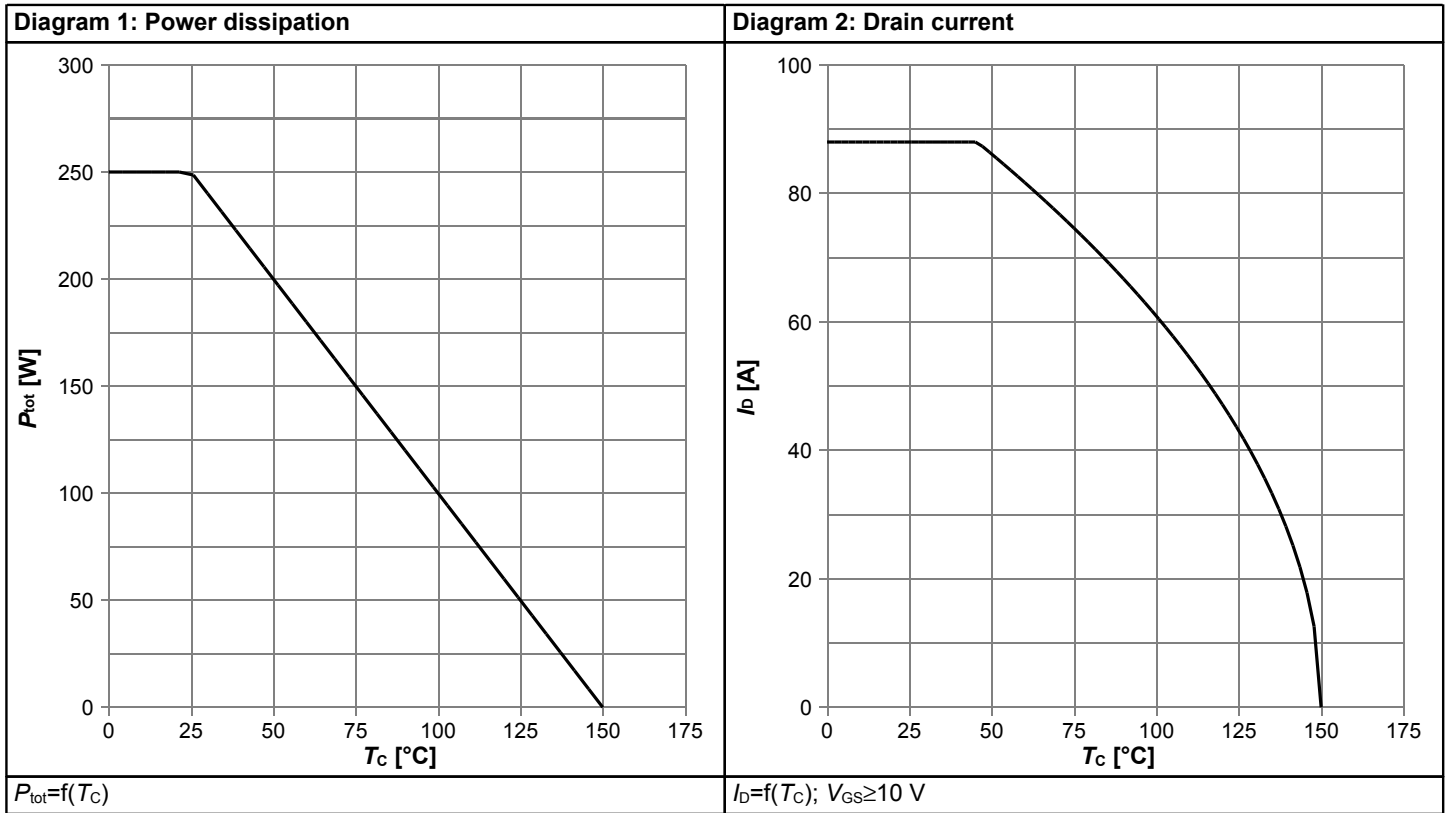
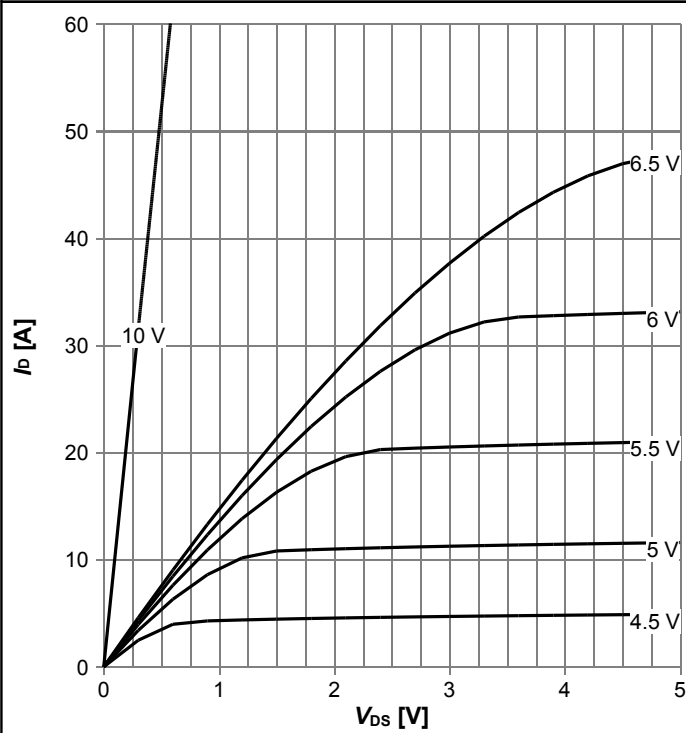
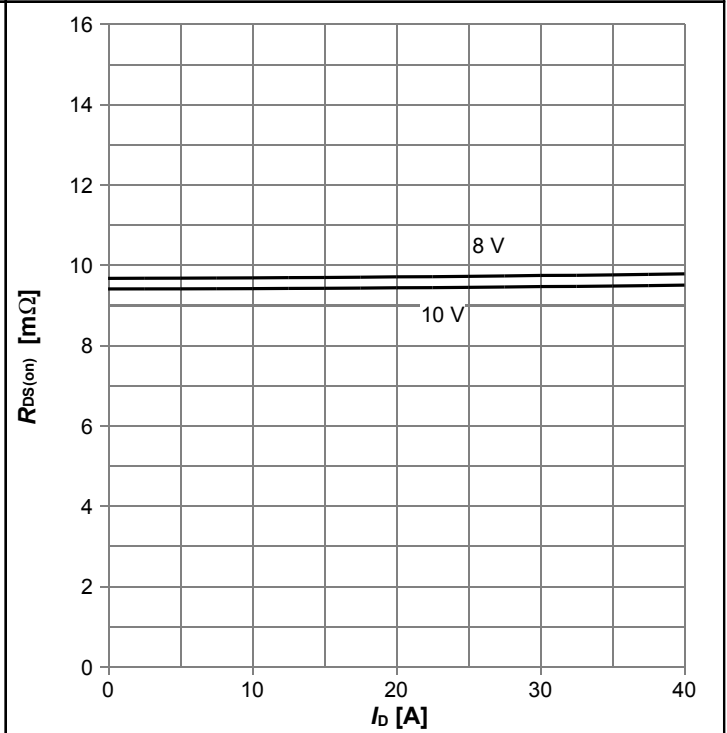


Diagram 5: Typ. output characteristics



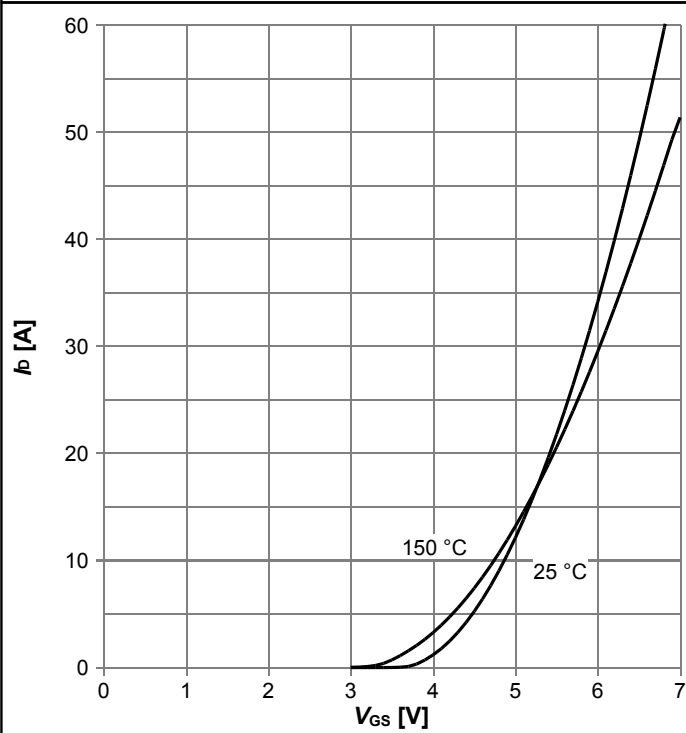
$I_D = f(V_{DS}); T_j = 25\text{ °C}, t_p = 30\text{ }\mu\text{s};$ parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



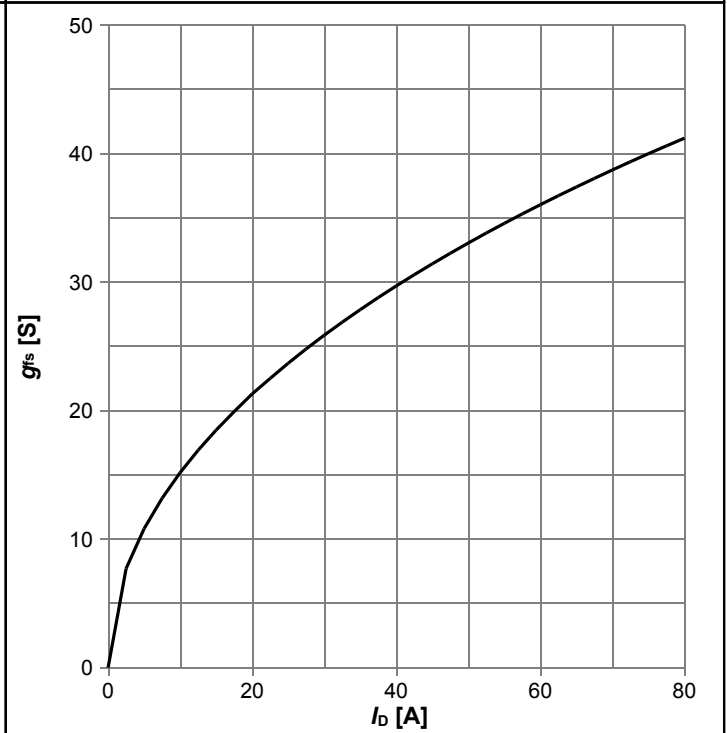
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



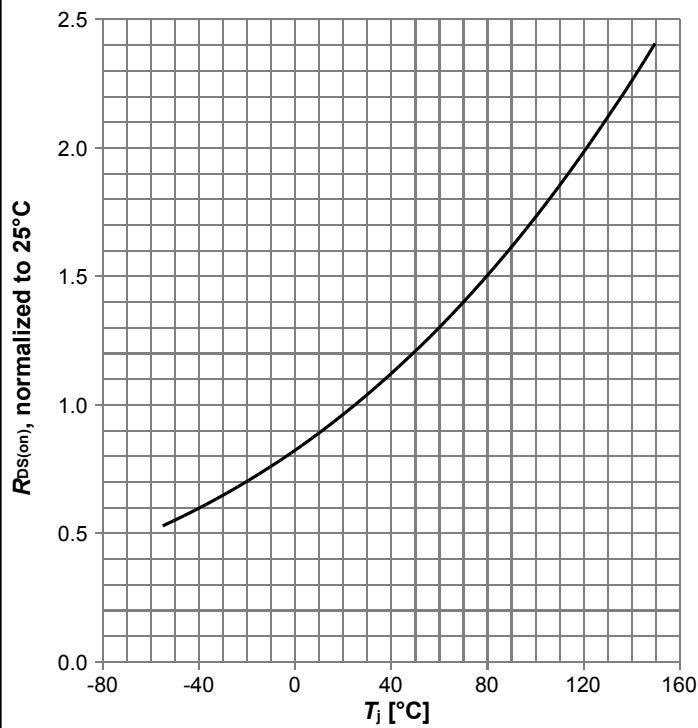
$I_D = f(V_{GS}); V_{DS} = 10\text{ V};$ parameter: T_j

Diagram 8: Typ. forward transconductance



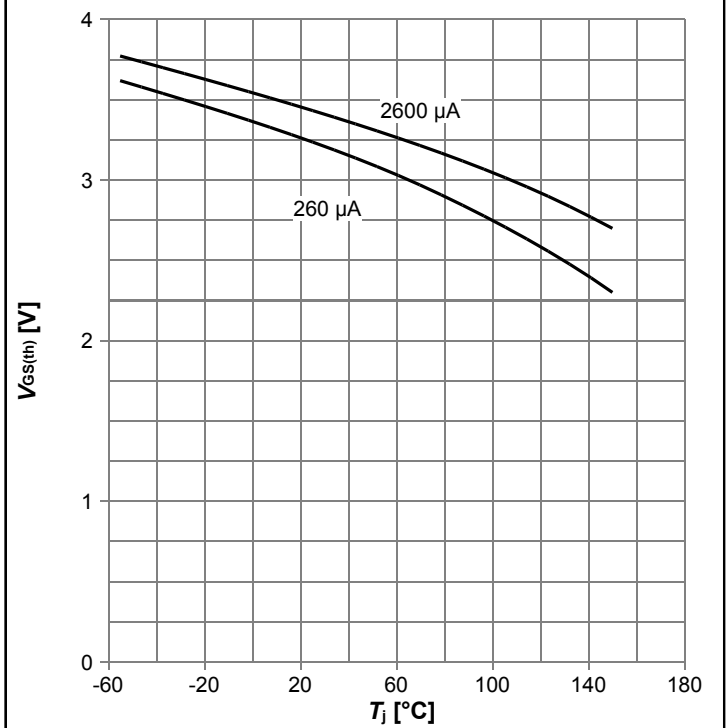
$g_{fs} = f(I_D); T_j = 25\text{ °C}$

Diagram 9: Normalized drain-source on-state resistance



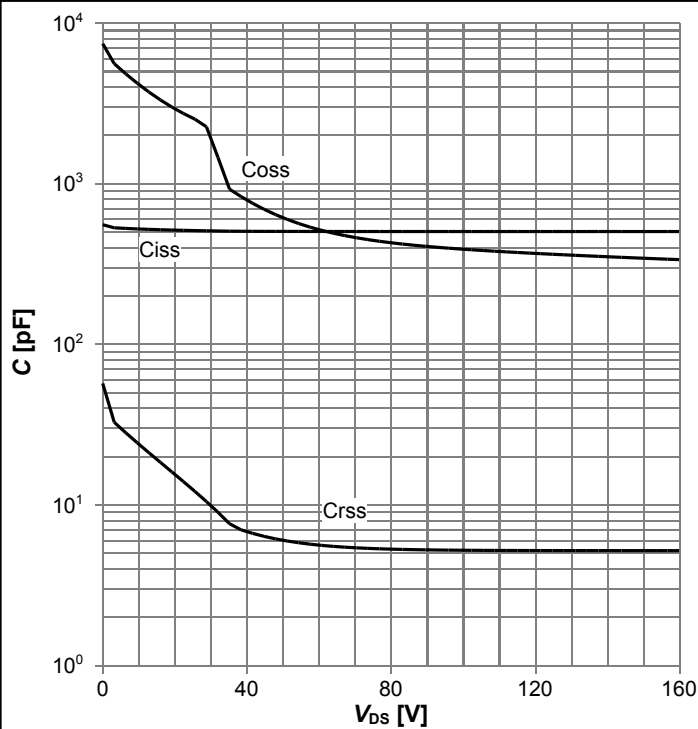
$R_{DS(on)}=f(T_j)$; $I_D=88$ A, $V_{GS}=10$ V

Diagram 10: Typ. gate threshold voltage



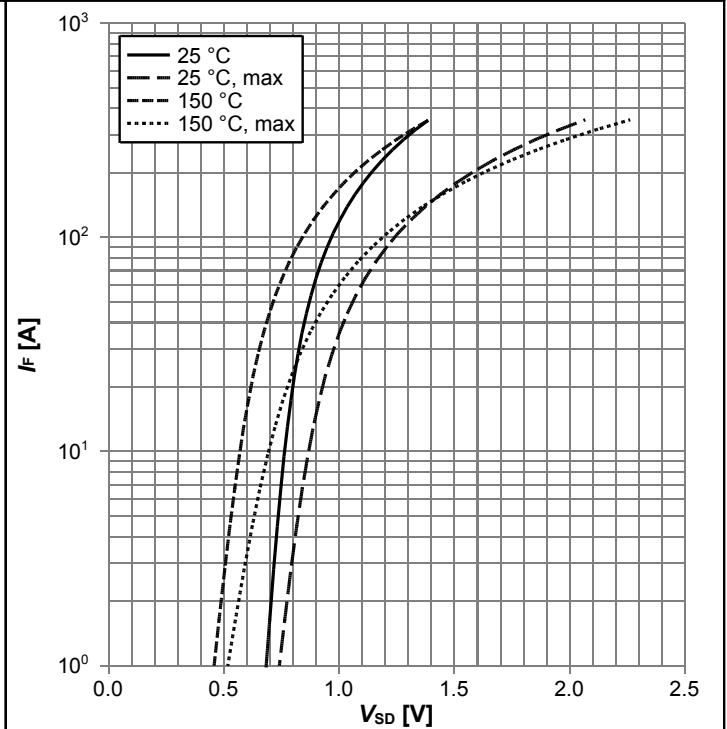
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



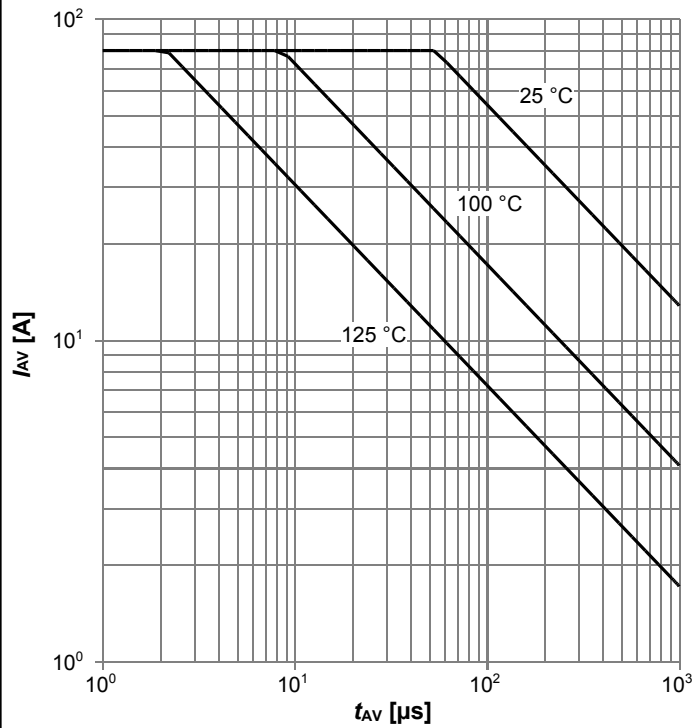
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

Diagram 12: Forward characteristics of reverse diode



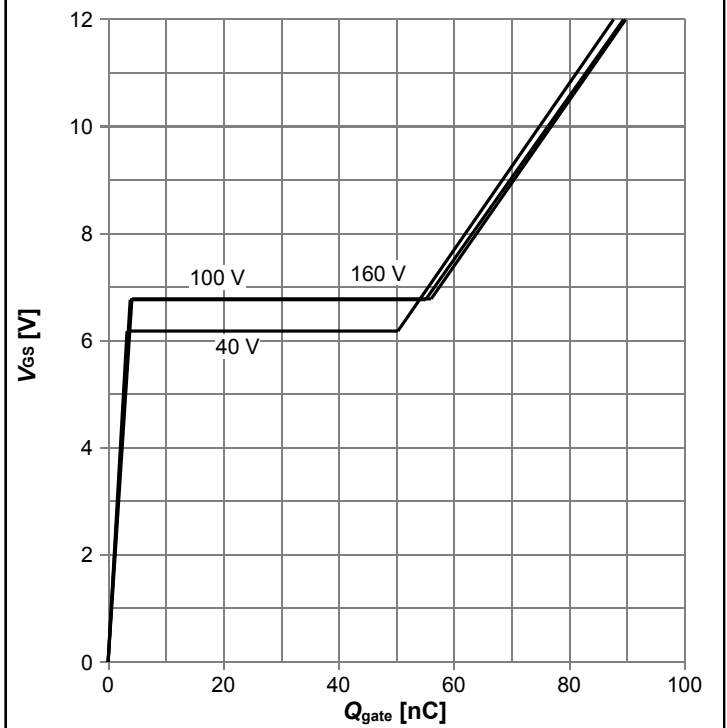
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



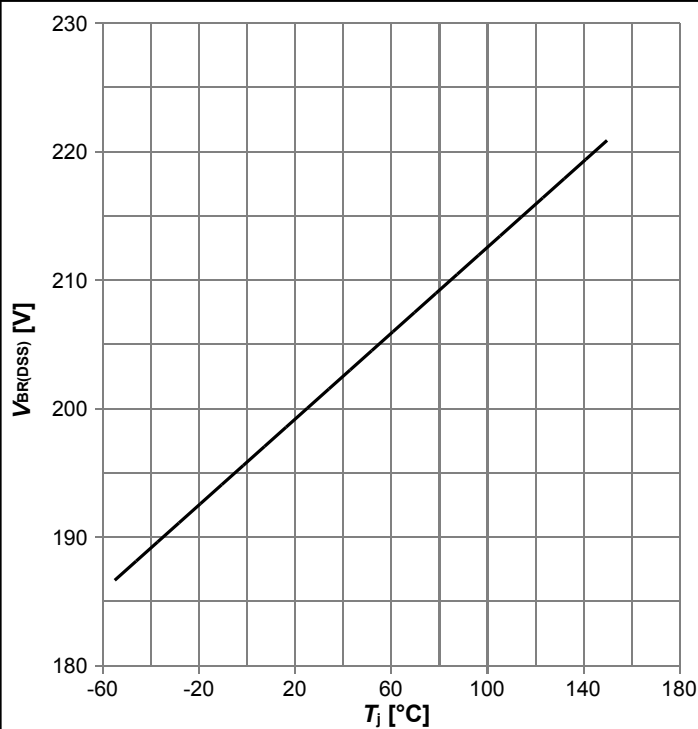
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



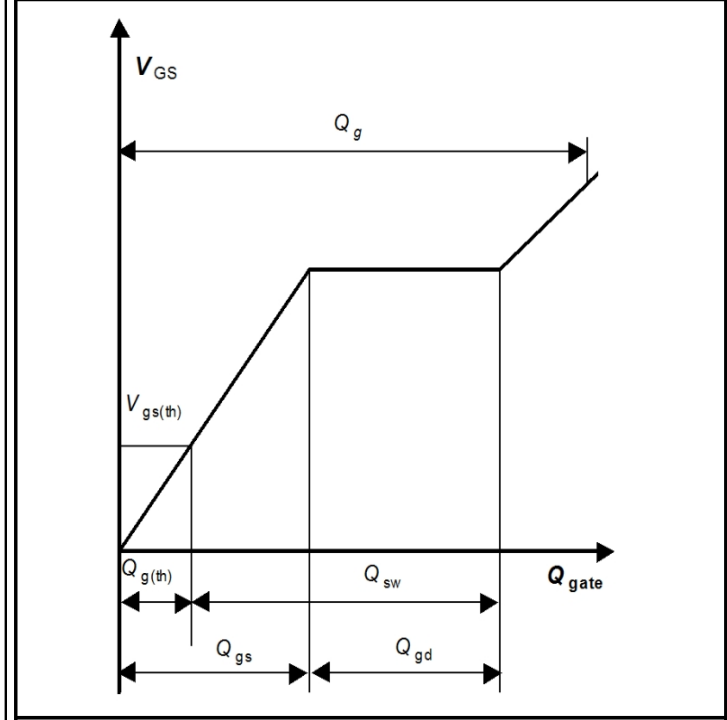
$V_{GS}=f(Q_{gate}); I_D=22 \text{ A}$ pulsed, resistive load; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Gate charge waveforms



5 Package Outlines



Figure 1 Outline PG-TO 263-3, dimensions in mm/inches

Revision History

IPB110N20N3LF

Revision: 2017-02-16, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-12-15	Release of final version
2.1	2017-02-16	Update technology heading

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